

## Product Summary

The GESDS15VFA1R is a uni-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data and power line.

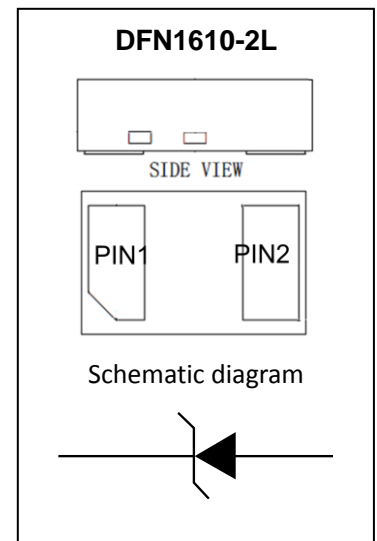
## Feature

- Low reverse stand-off voltage: 15.0V
- Low reverse clamping voltage
- Low leakage current
- Fast response time
- JESD22-A114-B ESD Rating of class 3B per human body model
- IEC 61000-4-2 Level 4 ESD protection

## Application

- Computers and peripherals
- Portable electronics
- Power lines
- Audio and video equipment
- Cellular handsets and accessories
- Other electronic equipment communication systems

## Marking: 15HA



## Absolute Maximum Ratings ( $T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
IEC 61000-4-2 ESD Voltage	$V_{\text{ESD}}^{1)}$	$\pm 30$	kV
IEC 61000-4-2 ESD Voltage		$\pm 30$	
JESD22-A114-B ESD Voltage		$\pm 16$	
ESD Voltage		$\pm 0.4$	
Peak Pulse Power	$P_{\text{PP}}^{2)}$	2000	W
Peak Pulse Current	$I_{\text{PP}}^{2)}$	60	A
Lead Solder Temperature – Maximum (10 Second Duration)	$T_L$	260	$^{\circ}\text{C}$
Junction Temperature	$T_j$	150	$^{\circ}\text{C}$
Storage Temperature	$T_{\text{stg}}$	-55~ +150	$^{\circ}\text{C}$

- 1) Device stressed with ten non-repetitive ESD pulses.
- 2) Non-repetitive current pulse 8/20 $\mu\text{s}$  exponential decay waveform according to IEC61000-4-5.

## ESD standards compliance

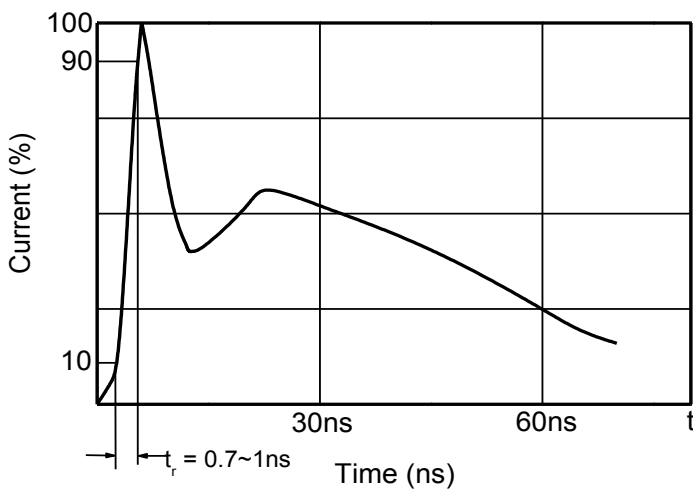
### IEC61000-4-2 Standard

Contact Discharge		Air Discharge	
Level	Test Voltage kV	Level	Test Voltage kV
1	2	1	2
2	4	2	4
3	6	3	8
4	8	4	15

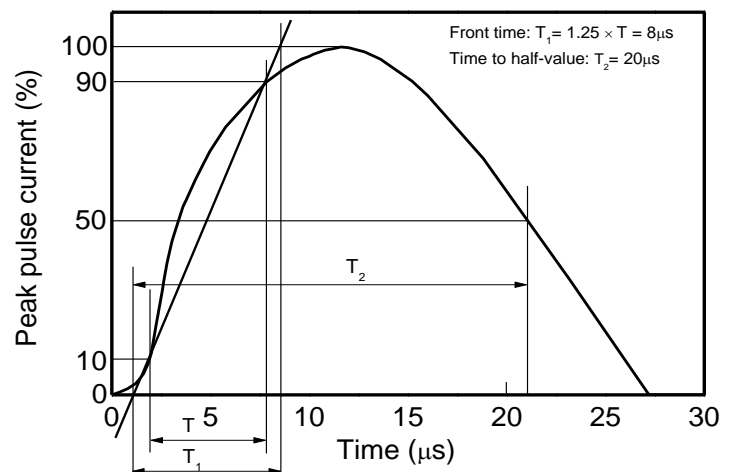
### JESD22-A114-B Standard

ESD Class	Human Body Discharge V
0	0~249
1A	250~499
1B	500~999
1C	1000~1999
2	2000~3999
3A	4000~7999
3B	8000~15999

### Contact discharge current waveform per IEC61000-4-2

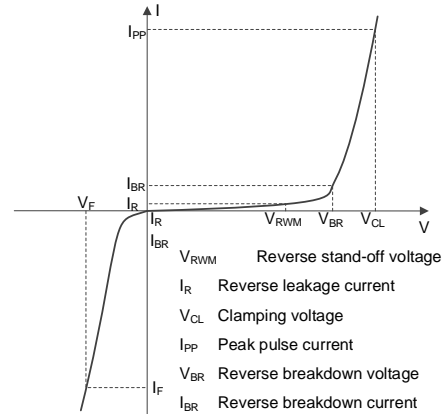


### 8/20 $\mu\text{s}$ waveform per IEC61000-4-5



## Electrical Parameter

Symbol	Parameter
V <sub>C</sub>	Clamping Voltage @ I <sub>PP</sub>
I <sub>PP</sub>	Peak Pulse Current
V <sub>BR</sub>	Breakdown Voltage @ I <sub>T</sub>
I <sub>T</sub>	Test Current
I <sub>R</sub>	Reverse Leakage Current @ V <sub>RWM</sub>
V <sub>RWM</sub>	Reverse Standoff Voltage



V-I characteristics for a Uni-directional TVS

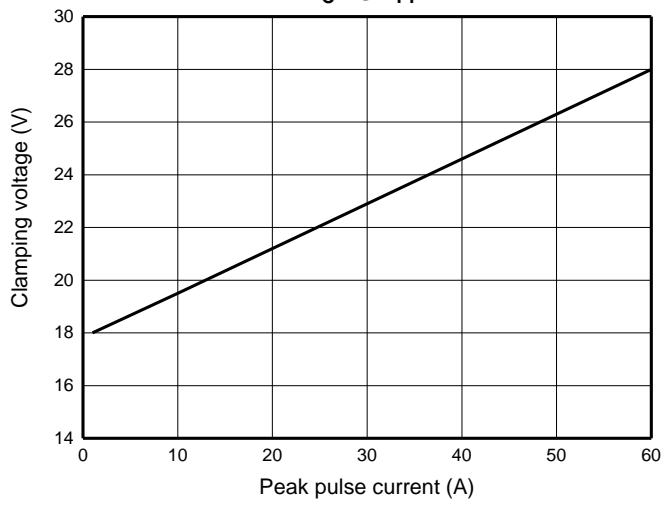
## Electrical Characteristics (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse stand-off voltage	V <sub>RWM</sub> <sup>1)</sup>				15	V
Reverse leakage current	I <sub>R</sub>	V <sub>RWM</sub> =15.0V			1	uA
Breakdown voltage	V <sub>BR</sub>	I <sub>T</sub> =1mA	16.5			V
Clamping voltage	V <sub>C</sub> <sup>2)</sup>	I <sub>PP</sub> =10A			22	V
		I <sub>PP</sub> =60A			32	V
Junction capacitance	C <sub>J</sub>	V <sub>R</sub> =0V, f=1MHz			450	pF

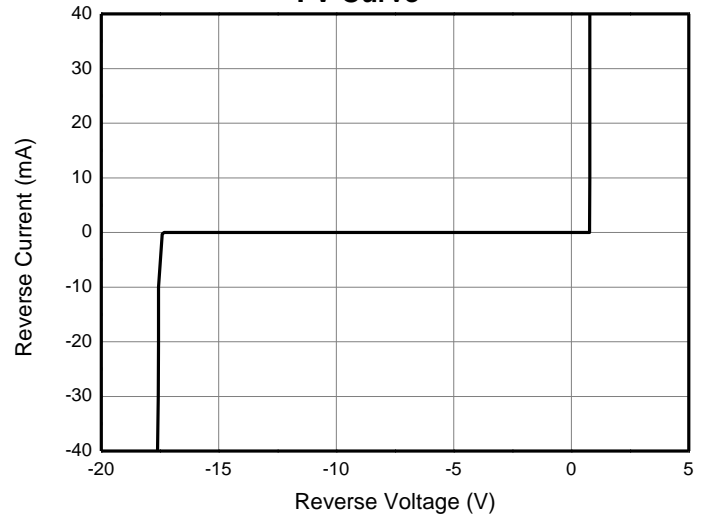
- 1) Other voltages available upon request.
- 2) Non-repetitive current pulse 8/20μs exponential decay waveform according to IEC61000-4-5

**Typical Characteristics**

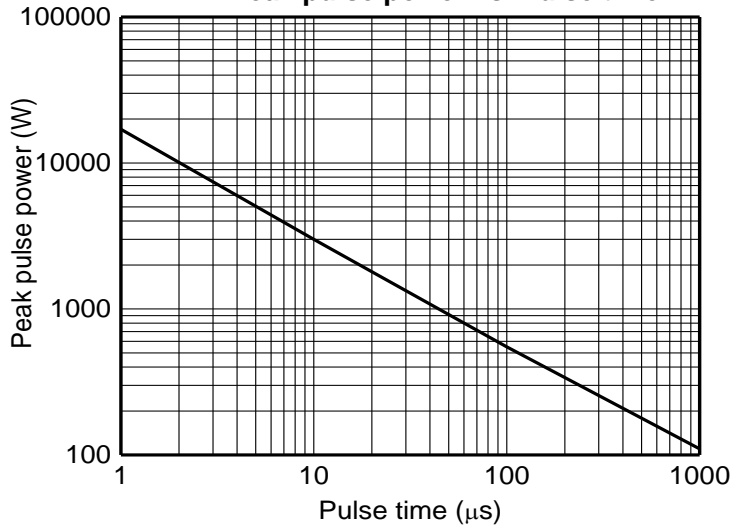
**$V_C$  vs.  $I_{PP}$**



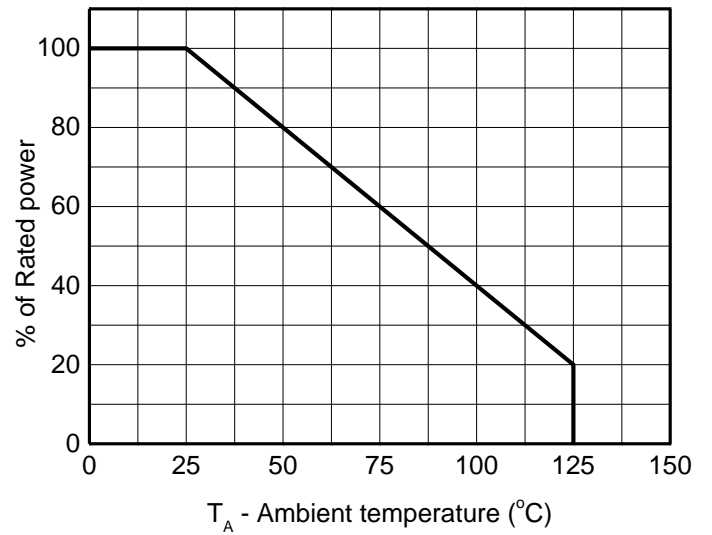
**I-V Curve**



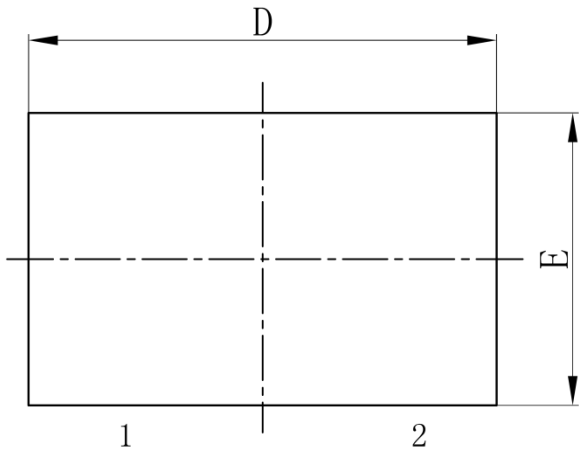
**Peak pulse power vs. Pulse time**



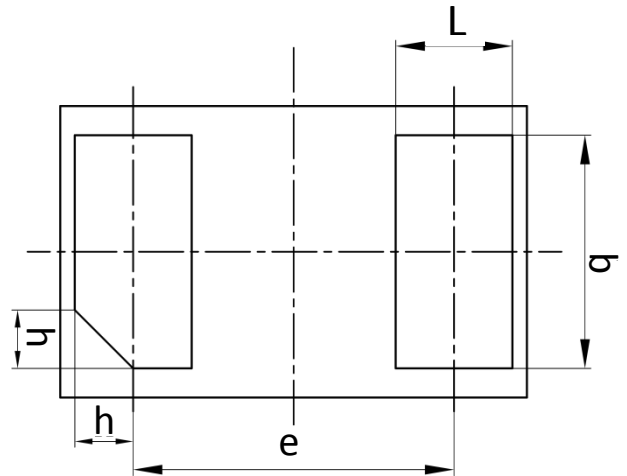
**Power derating vs. Ambient temperature**



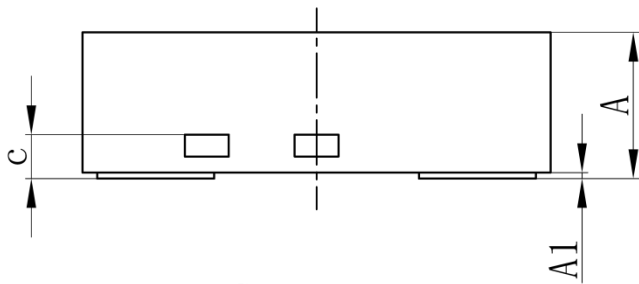
## DFN1610-2L Package Outline Dimensions



TOP VIEW



BOTTOM VIEW



SIDE VIEW

	Dimensions In Millimeters		
	Min.	Typ.	Max.
A	0.45	0.47	0.55
A1	-	0.03	0.05
b	0.75	0.78	0.95
c	0.10	0.12	0.20
D	1.55	1.60	1.65
e	-	1.10	-
E	0.95	1.00	1.05
L	0.35	0.40	0.45
h	0.15	0.20	0.25